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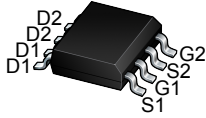


GDT

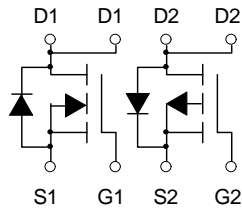


PLED

Product data sheet



SOP-8



N-Channel and P-Channel

Description

The AO4614-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

- $V_{DS} = 40V$ $I_D = 7.2A$
- $R_{DS(ON)} < 26m\Omega @ V_{GS}=10V$
- $V_{DS} = -40V$ $I_D = 6.5A$
- $R_{DS(ON)} < 54m\Omega @ V_{GS}=10V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	40	-40	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.2	-6.5	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.6	-5.1	A
I_{DM}	Pulsed Drain Current ²	23	-22	A
EAS	Single Pulse Avalanche Energy ³	16.2	39	mJ
I_{AS}	Avalanche Current	18	-28	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	1.67	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	75		$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	30		$^\circ C/W$

N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	---	---	V
BV _{DSS} /T _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.034	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5A	---	20	26	mΩ
		V _{GS} =4.5V, I _D =4A	---	28	33	
V _{GS(th)}	Gate Threshold Voltage		1.0	---	2.5	V
V _{GS(th)}	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =250uA	---	-4.56	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =32V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =32V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A	---	14	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.6	---	
Q _g	Total Gate Charge (4.5V)		---	5.5	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =20V, V _{GS} =4.5V, I _D =5A	---	1.25	---	
Q _{gd}	Gate-Drain Charge		---	2.5	---	
T _{d(on)}	Turn-On Delay Time		---	8.9	---	ns
T _r	Rise Time	V _{DD} =20V, V _{GS} =10V, R _G =3.3	---	2.2	---	
T _{d(off)}	Turn-Off Delay Time	I _D =1A	---	41	---	
T _f	Fall Time		---	2.7	---	
C _{iss}	Input Capacitance		---	593	---	pF
C _{oss}	Output Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	76	---	
C _{rss}	Reverse Transfer Capacitance		---	56	---	
I _S	Continuous Source Current ^{1,5}		---	---	6.1	A
I _{SM}	Pulsed Source Current ^{2,5}	V _G =V _D =0V, Force Current	---	---	23	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=18A
- 4.The power dissipation is limited by 150°C junction temperature
- 5 .The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40	---	---	V
BV _{DSS} /T _J	BV _{DSS} Temperature Coefficient	Reference to 25 °C, I _D =-1mA	---	-0.02	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-6A	---	45	54	mΩ
		V _{GS} =-4.5V, I _D =-4A	---	80	85	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	---	-2.5	V
V _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3.72	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-32V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-32V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-6A	---	13	---	S
Q _g	Total Gate Charge (-4.5V)		---	11.5	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-20V, V _{GS} =-4.5V, I _D =-6A	---	3.5	---	
Q _{gd}	Gate-Drain Charge		---	3.3	---	
T _{d(on)}	Turn-On Delay Time		---	22	---	ns
T _r	Rise Time	V _{DD} =-15V, V _{GS} =-10V, R _G =3.3Ω, I _D =-1A	---	15.7	---	
T _{d(off)}	Turn-Off Delay Time		---	59	---	
T _f	Fall Time		---	5.5	---	
C _{iss}	Input Capacitance		---	1415	---	pF
C _{oss}	Output Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	134	---	
C _{rss}	Reverse Transfer Capacitance		---	102	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-6	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	-22	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-28A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

N-Channel Typical Characteristics

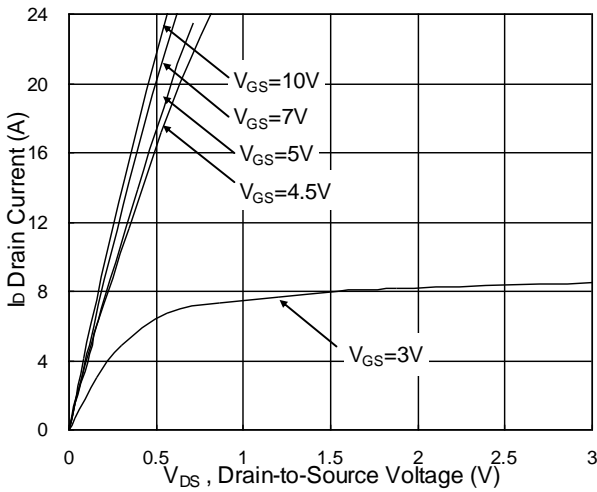


Fig.1 Typical Output Characteristics

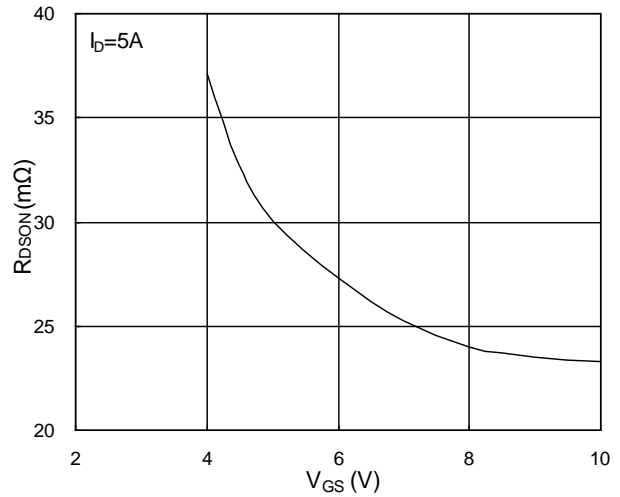


Fig.2 On-Resistance vs. G-S Voltage

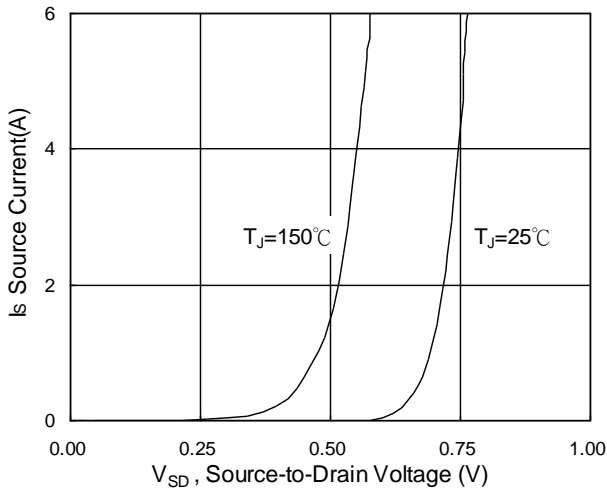


Fig.3 Forward Characteristics of Reverse

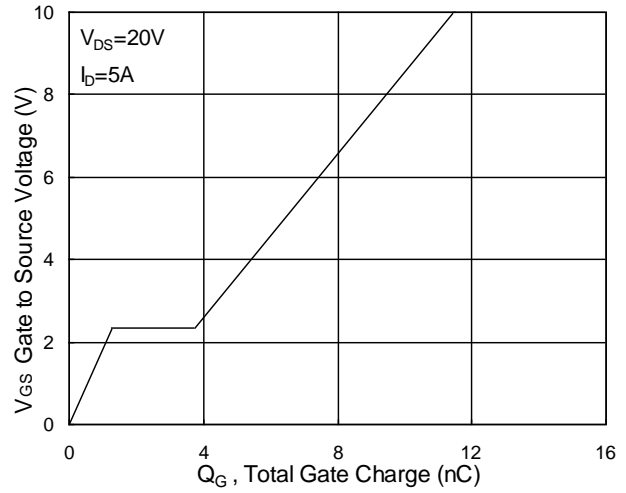


Fig.4 Gate-Charge Characteristics

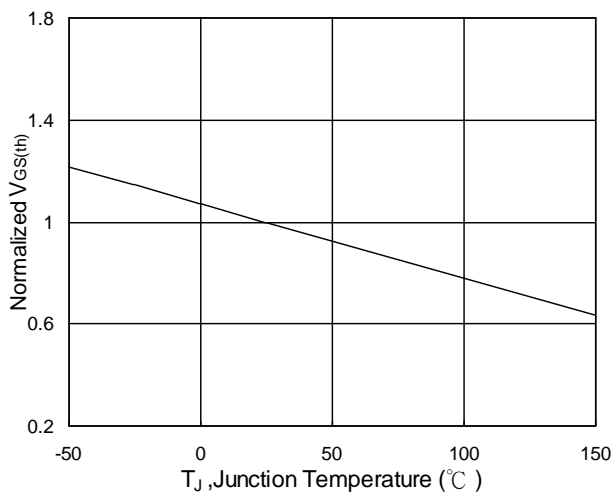


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

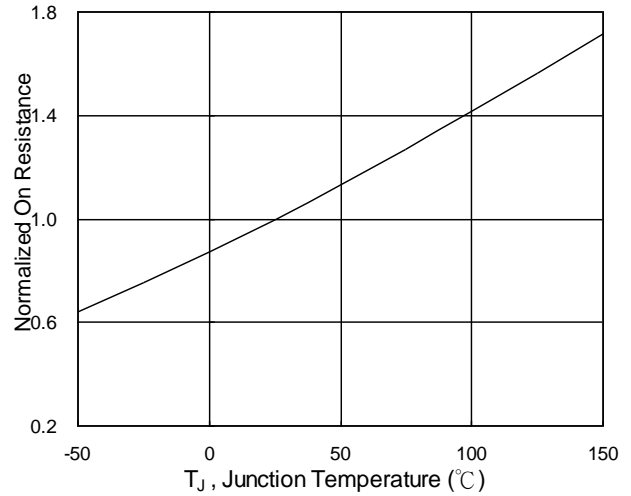


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

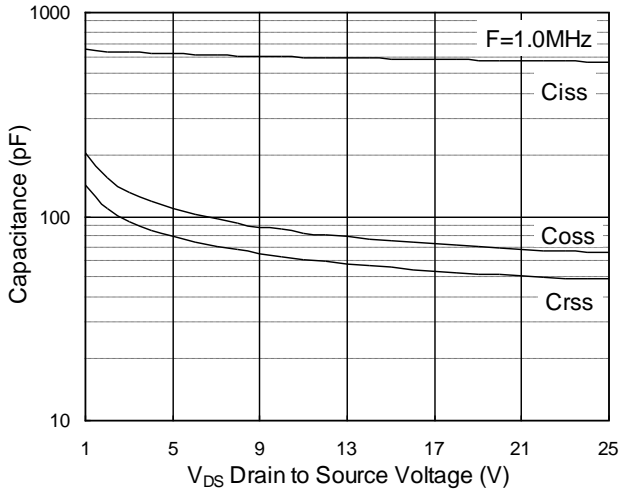


Fig.7 Capacitance

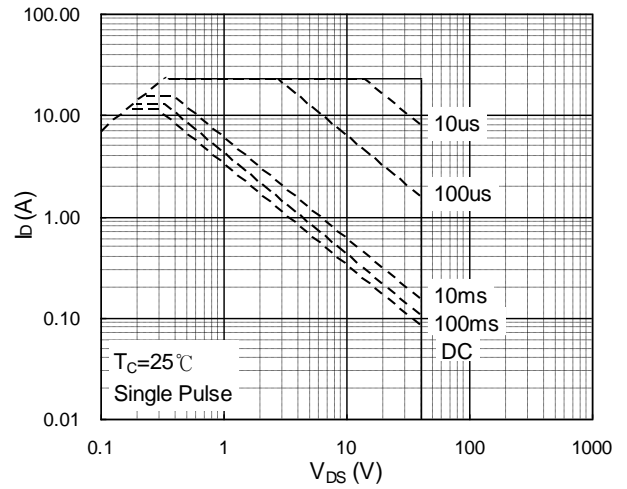


Fig.8 Safe Operating Area

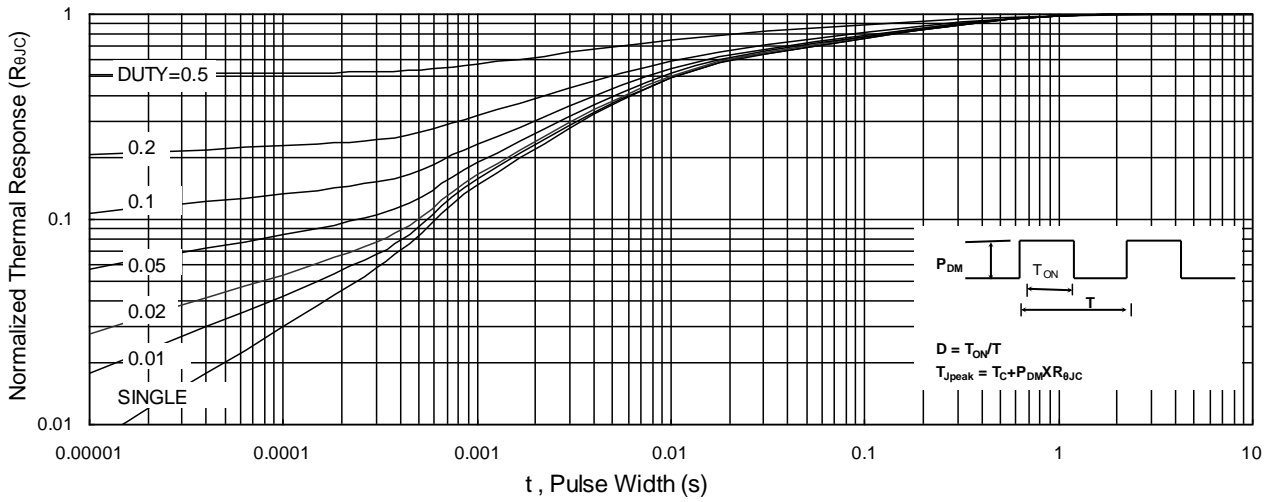


Fig.9 Normalized Maximum Transient Thermal Impedance

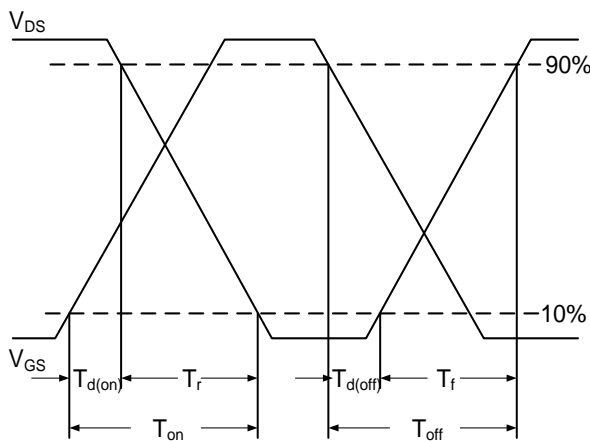


Fig.10 Switching Time Waveform

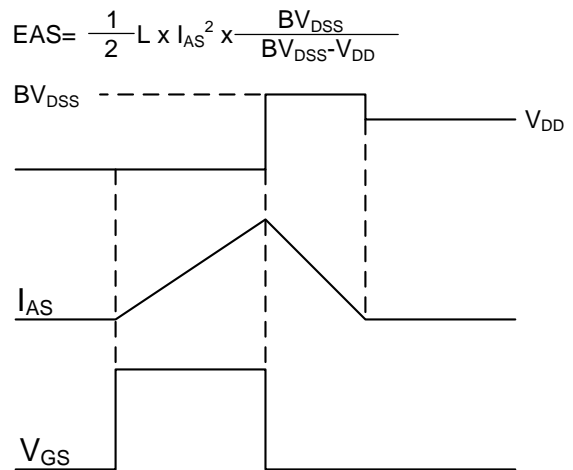


Fig.11 Unclamped Inductive Switching Wave

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

P-Channel Typical Characteristics

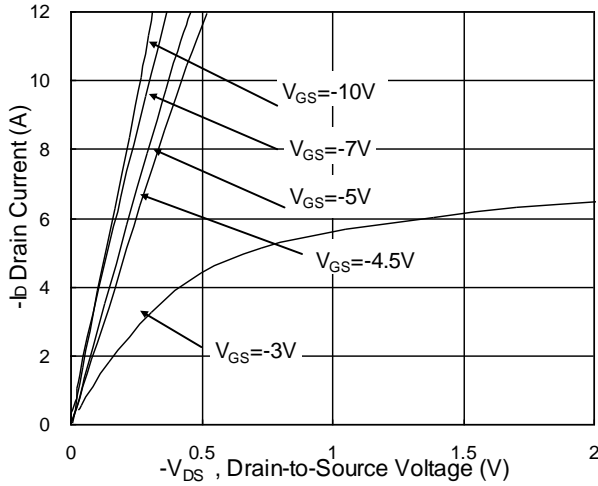


Fig.1 Typical Output Characteristics

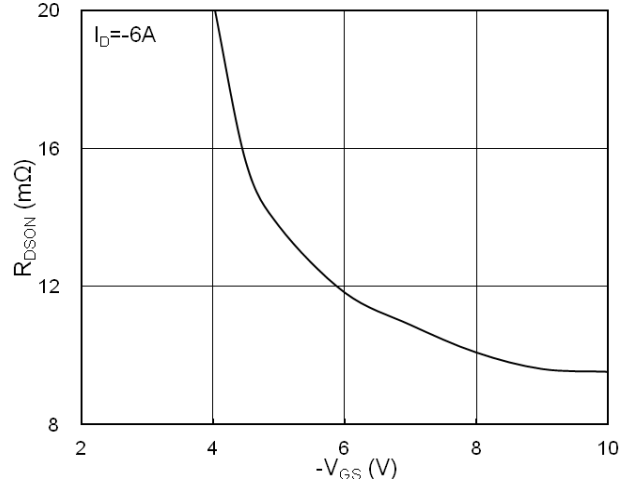


Fig.2 On-Resistance v.s Gate-Source

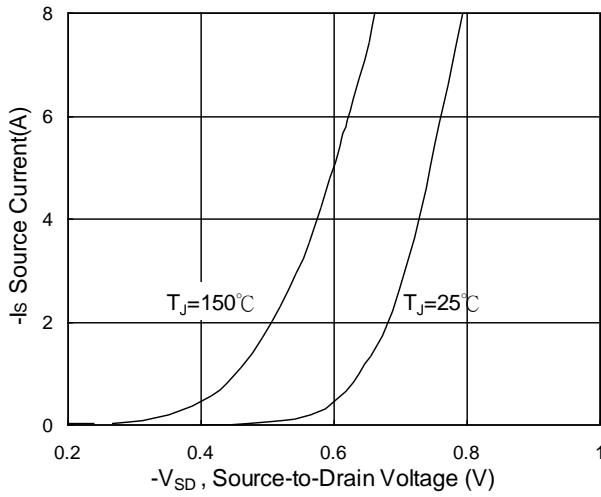


Fig.3 Forward Characteristics of Reverse

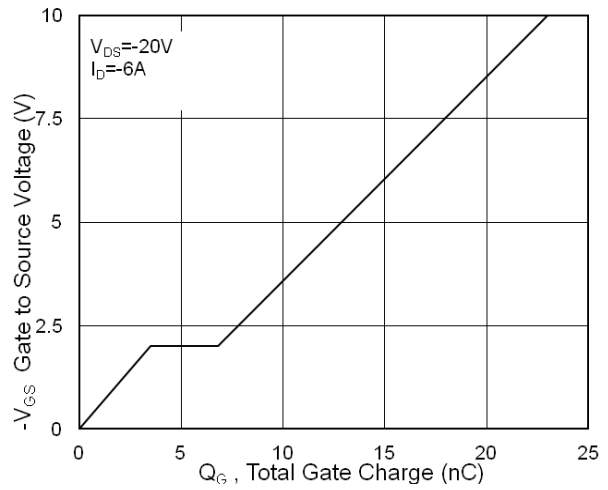


Fig.4 Gate-Charge Characteristics

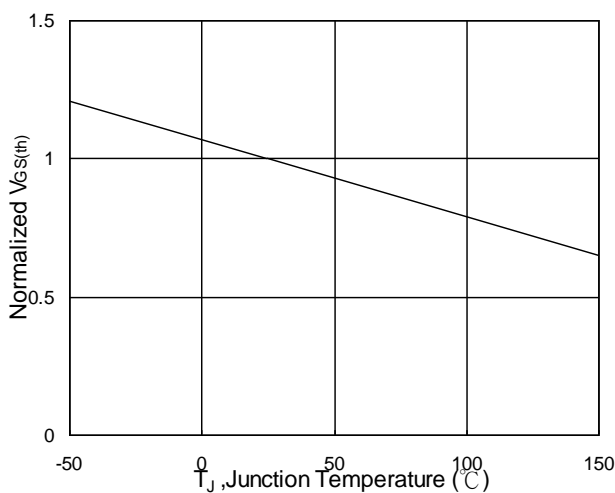


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

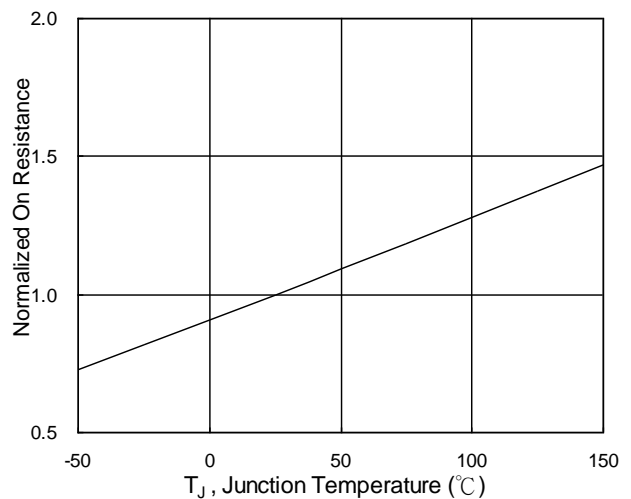


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

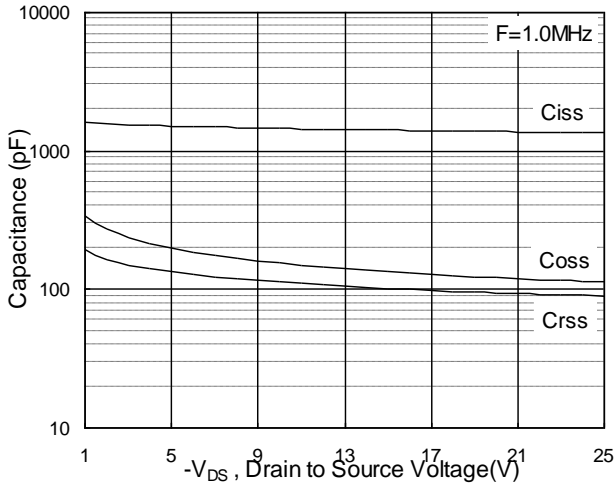


Fig.7 Capacitance

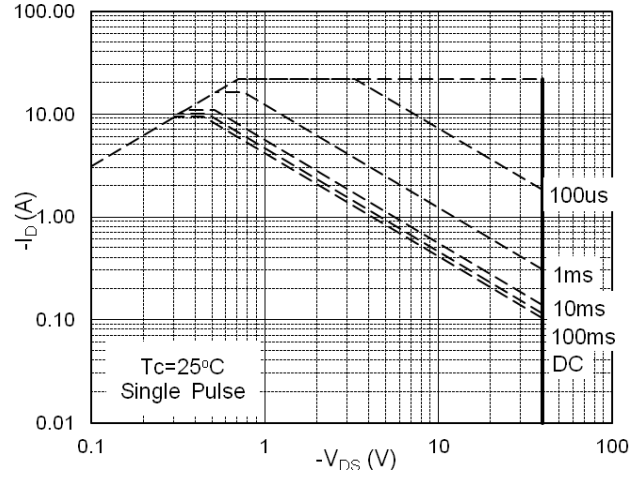


Fig.8 Safe Operating Area

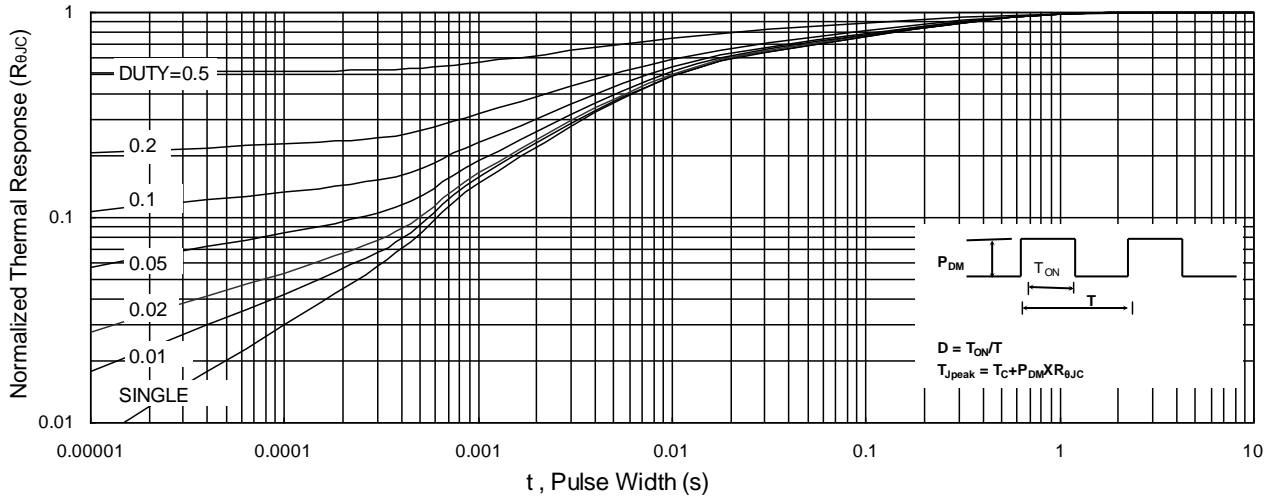


Fig.9 Normalized Maximum Transient Thermal Impedance

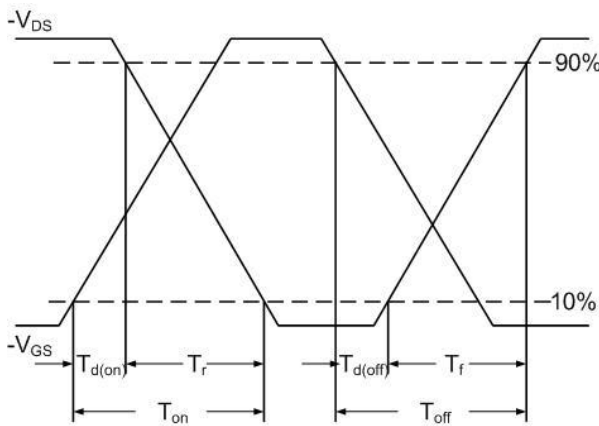


Fig.10 Switching Time Waveform

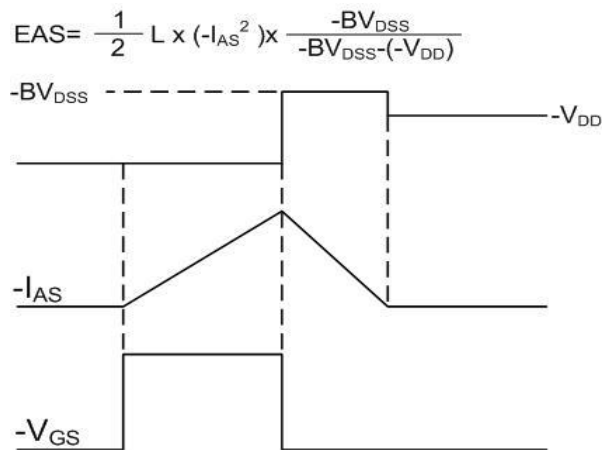
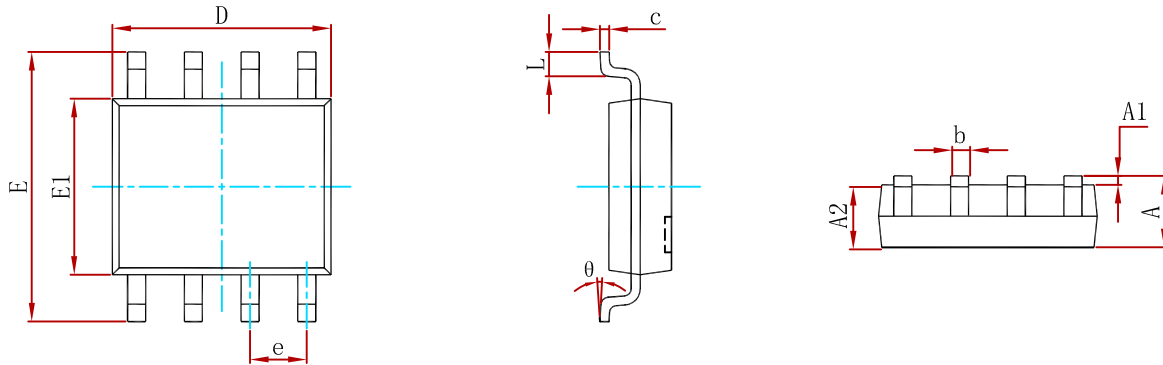


Fig.11 Unclamped Inductive Waveform

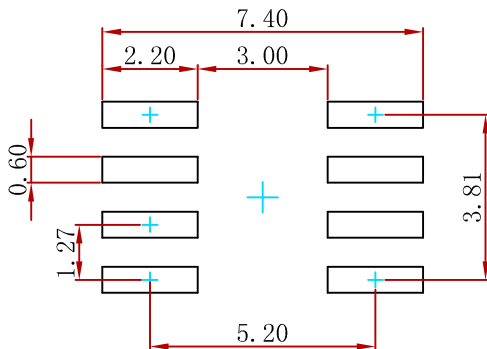
$$EAS = \frac{1}{2} L \times (-I_{AS}^2) \times \frac{-BV_{DSS}}{-BV_{DSS} - (-V_{DD})}$$

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO4614-MS	SOP-8	3000

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